

isc Silicon NPN Power Transistor

BU2725AW

DESCRIPTION

- Collector-Emitter Sustaining Voltage-
: $V_{CEO(SUS)} = 825V$ (Min)
- High Switching Speed

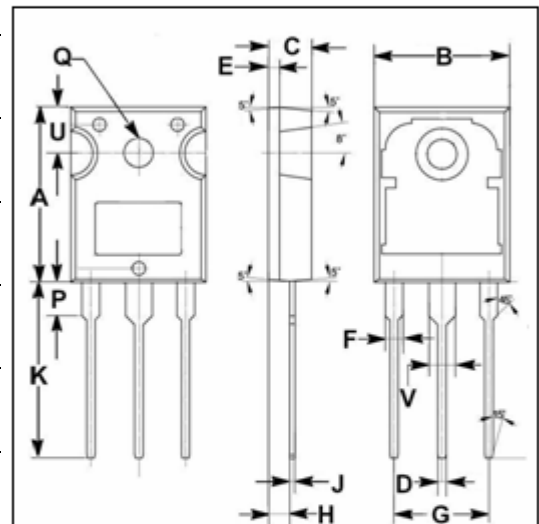
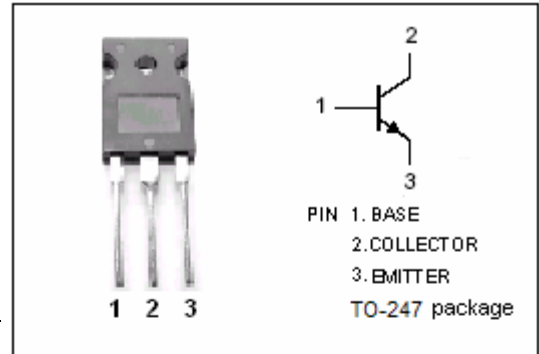
APPLICATIONS

- Designed for use in horizontal deflection circuits of color TV receivers.

ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ C$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CES}	Collector- Emitter Voltage($V_{BE} = 0$)	1700	V
V_{CEO}	Collector-Emitter Voltage	825	V
V_{EBO}	Emitter-Base Voltage	7.5	V
I_C	Collector Current- Continuous	12	A
I_{CM}	Collector Current-Peak	30	A
I_B	Base Current- Continuous	12	A
I_{BM}	Base Current-Peak	20	A
P_C	Collector Power Dissipation @ $T_C=25^\circ C$	125	W
T_J	Junction Temperature	150	$^\circ C$
T_{stg}	Storage Temperature Range	-65~150	$^\circ C$

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j-c}$	Thermal Resistance, Junction to Case	2.8	$^\circ C/W$



DIM	mm	
	MIN	MAX
A	19.80	20.20
B	15.40	15.80
C	4.90	5.10
D	0.90	1.10
E	1.40	1.60
F	1.90	2.10
G	10.80	11.00
H	2.40	2.60
J	0.50	0.70
K	19.50	20.50
P	3.90	4.10
Q	3.30	3.50
U	5.20	5.40
V	2.90	3.10

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ELECTRICAL CHARACTERISTICS

 $T_C=25^{\circ}\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CEO(SUS)}$	Collector-Emitter Sustaining Voltage	$I_C=100\text{mA}$; $I_B=0$, $L=25\text{mH}$	825			V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	$I_E=1\text{mA}$; $I_C=0$	7.5			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C=7\text{A}$; $I_B=1.75\text{A}$			1.0	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C=7\text{A}$; $I_B=1.75\text{A}$			1.1	V
I_{CES}	Collector Cutoff Current	$V_{CE}=1700\text{V}$; $V_{BE}=0$ $V_{CE}=1700\text{V}$; $V_{BE}=0$; $T_C=125^{\circ}\text{C}$			1.0 2.0	mA
I_{EBO}	Emitter Cutoff Current	$V_{EB}=7.5\text{V}$; $I_C=0$			1.0	mA
h_{FE-1}	DC Current Gain	$I_C=0.1\text{A}$; $V_{CE}=5\text{V}$		22		
h_{FE-2}	DC Current Gain	$I_C=7\text{A}$; $V_{CE}=1\text{V}$	4		8.5	